

Title (en)
MATERIAL FOR CHEMICAL VAPOR DEPOSITION, SILICON-CONTAINING INSULATING FILM AND PROCESS FOR PRODUCTION THEREOF

Title (de)
MATERIAL FÜR GASPHASENABSCHEIDUNG, SILICIUMHALTIGER ISOLIERFILM UND HERSTELLUNGSVERFAHREN DAFÜR

Title (fr)
MATÉRIAU POUR DÉPOSITION EN PHASE GAZEUSE PAR UN PROCÉDÉ CHIMIQUE, FILM ISOLANT CONTENANT DU SILICIUM ET SON PROCÉDÉ DE PRODUCTION

Publication
EP 2264219 A4 20120905 (EN)

Application
EP 09725410 A 20090324

Priority

- JP 2009055825 W 20090324
- JP 2008079734 A 20080326
- JP 2008124327 A 20080512
- JP 2008225736 A 20080903
- JP 2008225735 A 20080903
- JP 2008233115 A 20080911

Abstract (en)
[origin: EP2264219A1] A chemical vapor deposition material includes an organosilane compound shown by the following general formula (1). wherein R 1 and R 2 individually represent a hydrogen atom, an alkyl group having 1 to 4 carbon atoms, a vinyl group, or a phenyl group, R 3 and R 4 individually represent an alkyl group having 1 to 4 carbon atoms, an acetyl group, or a phenyl group, m is an integer from 0 to 2, and n is an integer from 1 to 3.

IPC 8 full level
C23C 16/42 (2006.01); **C08G 77/50** (2006.01); **H01L 21/312** (2006.01); **H01L 21/316** (2006.01); **H01L 21/768** (2006.01); **H01L 23/522** (2006.01)

CPC (source: EP US)
C07F 7/1804 (2013.01 - EP US); **C23C 16/401** (2013.01 - EP US); **H01L 21/02126** (2013.01 - US); **H01L 21/02203** (2013.01 - US); **H01L 21/02211** (2013.01 - EP US); **H01L 21/02274** (2013.01 - US); **H01L 21/31633** (2016.02 - US); **H01L 21/31695** (2016.02 - US); **H01L 21/02126** (2013.01 - EP); **H01L 21/02203** (2013.01 - EP); **H01L 21/02216** (2013.01 - EP); **H01L 21/02274** (2013.01 - EP); **H01L 23/5329** (2013.01 - EP US); **H01L 2924/0002** (2013.01 - EP US)

C-Set (source: EP US)
H01L 2924/0002 + H01L 2924/00

Citation (search report)

- [X] US 2007173071 A1 20070726 - AFZALI-ARDAKANI ALI [US], et al
- [X] US 2006058487 A1 20060316 - RANTALA JUHA T [FI], et al
- [X] EP 1691410 A2 20060816 - AIR PROD & CHEM [US]
- [X] EP 1705208 A1 20060927 - JSR CORP [JP]
- See references of WO 2009119583A1

Cited by
NL2007705A; WO2013066184A1; WO2011103282A2; US8932674B2; EP3535438A4; EP4307343A3

Designated contracting state (EPC)
AT BE BG CH CY CZ DE DK EE ES FI FR GB GR HR HU IE IS IT LI LT LU LV MC MK MT NL NO PL PT RO SE SI SK TR

DOCDB simple family (publication)
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DOCDB simple family (application)
EP 09725410 A 20090324; CN 200980104520 A 20090324; JP 2009055825 W 20090324; JP 2010505676 A 20090324; KR 20107018948 A 20090324; TW 98109863 A 20090326; US 93480609 A 20090324